

# TAS5731M Improvements from TAS5731

- TAS5731M was improved to focus on improved SOA margin at high PVDD and improved reliability
  - Improved BST diode component
    - Larger LDMOS component for higher voltage/current handling
  - Improved overcurrent scheme
    - Better correlation of OC threshold between terminal-to-terminal and terminal-to-rail
  - Improved gate drive
    - Reduced spike voltage results in more margin during high voltage operation
  - Added BST\_UVP protection feature
  - Added PPSC protection feature (pin to pin short circuit at power-up)
    - Protects against PCB assembly defects such as solder short
    - Device remains in hi-z in the presence of a short to avoid destructive failures at power-up
- TI Recommends that TAS5731M be used in all new designs